

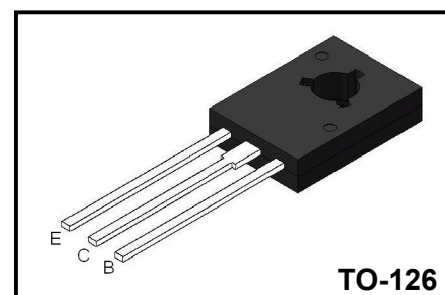
PNP Plastic-Encapsulate Transistors

Application

◆High-DefinitionCRT Display, Video Output

Features

- ◆High breakdown voltage : $BV_{CEO} \geq 300V$
- ◆Complementary is 2KTC3503



TO-126

Absolute Maximum Ratings ($T_A=25^\circ C$)

Parameter	Symbol	Rating	Unit
Collector-Base Voltage	BV_{CBO}	-300	V
Collector-Emitter Voltage	BV_{CEO}	-300	V
Emitter-Base Voltage	BV_{EBO}	-5	V
Collector Current	I_C	-100	mA
Collector Power Dissipation	P_C	1.5	W
Junction Temperature	T_j	150	$^\circ C$
Storage Temperature	T_{stg}	-55~150	$^\circ C$

Electrical Characteristics ($T_A=25^\circ C$)

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage	BV_{CBO}	$I_C = 100\mu A, I_E = 0$	-300			V
Collector-emitter voltage	BV_{CEO}	$I_C = -1mA, I_B = 0$	-300			V
Emitter-base voltage	BV_{EBO}	$I_E = -100\mu A, I_C = 0$	-5			V
Collector cut-off current	I_{CBO}	$V_{CB} = -200V, I_E = 0$			-0.1	μA
Emitter cut-off current	I_{EBO}	$V_{EB} = -4V, I_C = 0$			-0.1	μA
DC current gain	h_{FE}	$V_{CE} = -10V, I_C = -10mA$	60		200	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = -20mA, I_B = -2mA$			-0.6	V
Base -emitter saturation voltage	$V_{BE(sat)}$	$I_C = -20mA, I_B = -2mA$			-1.0	V
Transition frequency	f_T	$V_{CE} = -30V, I_C = -10mA$		140		MHz
Output capacitance	C_{ob}	$V_{CB} = -30V, I_E = 0, f=1MHz$		3.1		pF

h_{FE} Classification

Classification	KTA1381-O	KTA1381-Y
Range	60~120	100~200

Typical Characteristics

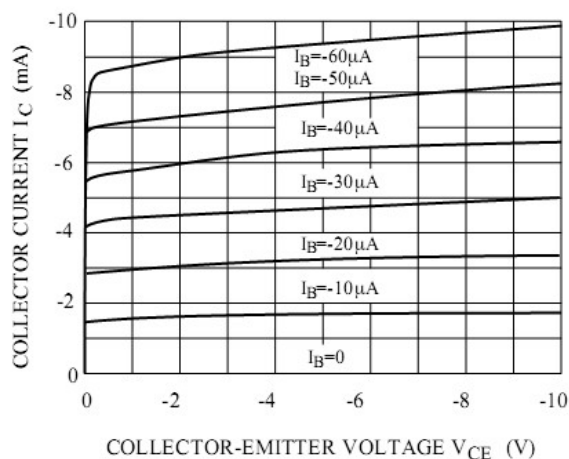


Figure.1. Typical Output Characteristics

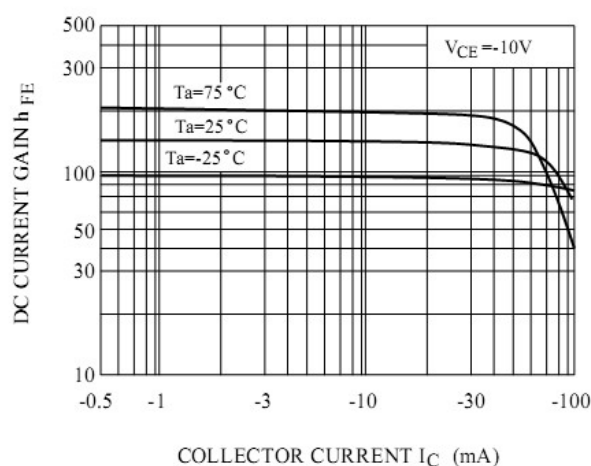


Figure.2. DC current Gain

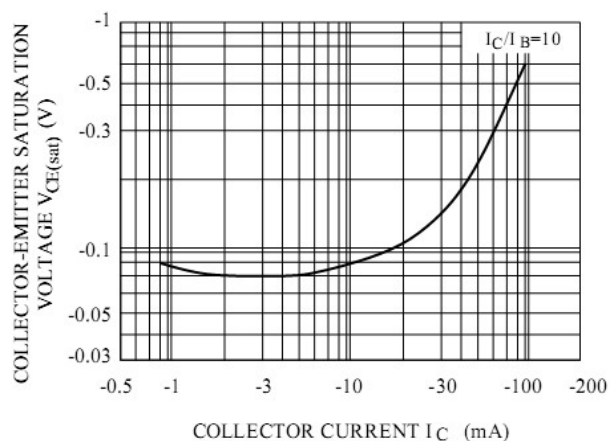


Figure.3. Collector to Emitter Saturation Voltage

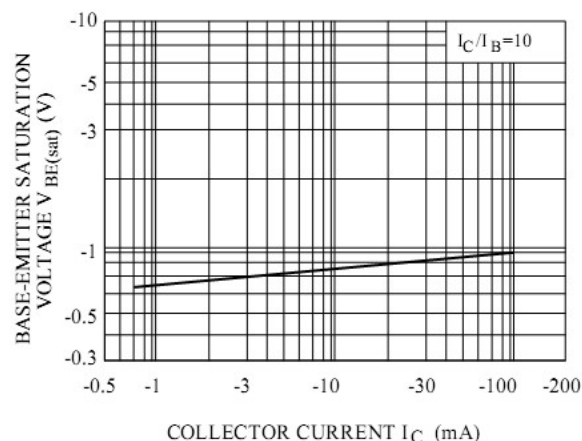


Figure.4. Base to Emitter Saturation Voltage

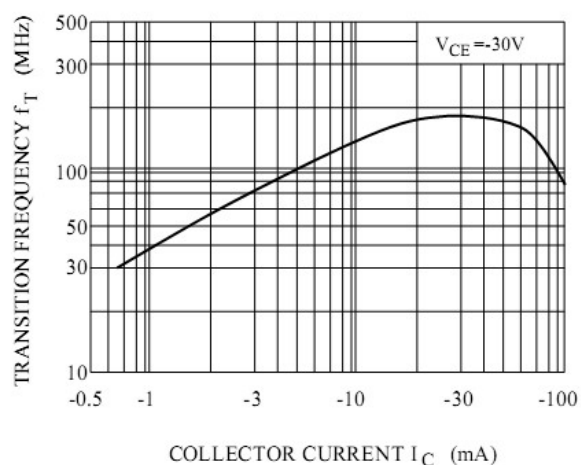


Figure.5. Gain Bandwidth Product

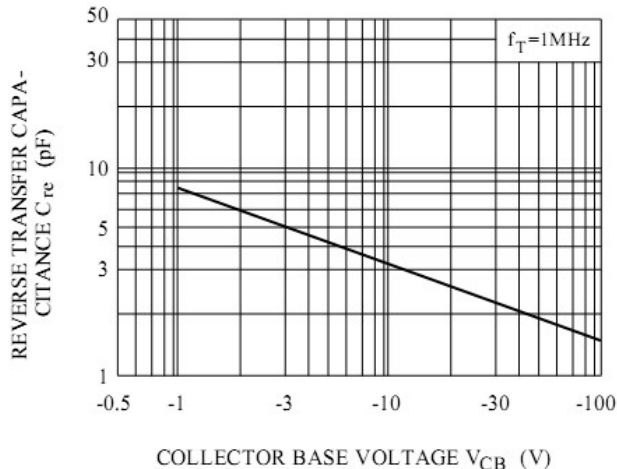


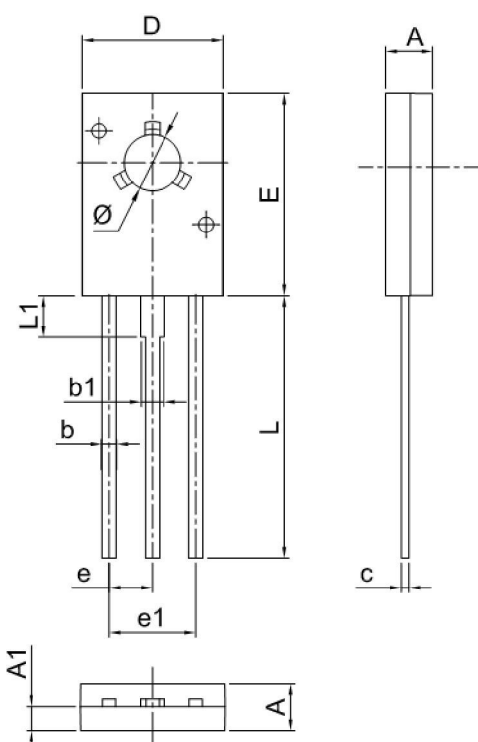
Figure.6. Collector Output Capacitance

Ordering information

Package	Packing Description	Base Quantity
TO-126	Bulk	500pcs/Bag

Package Dimensions

TO-126

	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	2.40	2.80	0.094	0.110
A1	1.00	1.40	0.039	0.055
b	0.66	0.86	0.026	0.034
b1	1.17	1.37	0.046	0.054
c	0.40	0.60	0.016	0.024
D	7.30	7.70	0.287	0.303
E	10.60	11.00	0.417	0.433
e	2.25	2.33	0.089	0.092
e1	4.50	4.66	0.177	0.183
L	14.00	15.00	0.551	0.591
L1	1.90	2.50	0.075	0.098
Φ	3.10	3.30	0.122	0.130

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